Abstracts

Field Analysis and Design Criteria for T-Gate TW-FET's with Positive Gain

M. Farina, L. Pierantoni and T. Rozzi. "Field Analysis and Design Criteria for T-Gate TW-FET's with Positive Gain." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1269-1272.

We present an accurate e.m model of T-Gate TW-FET's and necessary conditions for obtaining exponentially growing waves. This model takes into detailed account device geometry, the effect of carrier velocity saturation in the high field region, conductor and dielectric losses and small signal channel current.

❑ Return to main document.